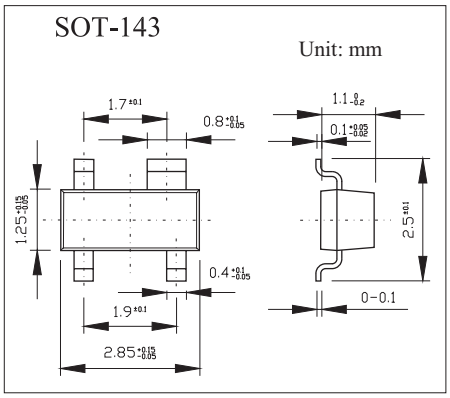
Silicon RF Switching Diodes

BAR81



Features

- Design for use in shunt configuration
- High shunt signal isolation
- Low shunt insertion loss

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	30	V
Forward current	I_F	100	mA
Junction temperature	T_j	150	℃
Operating temperature range	T_{op}	-55 to +125	℃
Storage temperature	T_{stg}	-55 to +150	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current	I_R	V_R = 20 V			20	nA
Forward voltage	V_F	I_F = 100 mA		0.93	1	V
Diode capacitance	C_T	V_R = 1 V, f = 1 MHz		0.6		pF
		V_R = 3 V, f = 1 MHz		0.57		
Forward resistance	rf	I_F = 5 mA, f = 100 MHz		0.7		Ω
Series inductance chip to ground	L_S			1.5		nH

Marking

Type	BAR81
Marking	BBs